

PUMB16,115 Datasheet





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DiGi Electronics Part Number PUMB16,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PUMB16,115

Description TRANS PREBIAS 2PNP 50V 6TSSOP

Detailed Description Pre-Biased Bipolar Transistor (BJT) 2 PNP - Pre-Bias ed (Dual) 50V 100mA 300mW Surface Mount 6-TSS

OP



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PUMB16,115	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
2 PNP - Pre-Biased (Dual)	100mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50V	22kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
47kOhms	80 @ 5mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
150mV @ 500μA, 10mA	1μΑ
Frequency - Transition:	Power - Max:
	300mW
Grade:	Qualification:
Automotive	AEC-Q100
Mounting Type:	Package / Case:
Surface Mount	6-TSSOP, SC-88, SOT-363
Supplier Device Package:	Base Product Number:
6-TSSOP	PUMB16

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

Rev. 03 — 31 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP resistor-equipped transistors

Table 1. Product overview

Type number	pe number Package		NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB16	SOT666	-	PEMD16	PEMH16	
PUMB16	SOT363	SC-88	PUMD16	PUMH16	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	



PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

2. Pinning information

Table 3. Pinning

Table 3.	riiiiiig		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa212

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB16	-	plastic surface mounted package; 6 leads	SOT666
PUMB16	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMB16	5G
PUMB16	B*7

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
V_{I}	input voltage				
	positive		-	+7	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1] [2] -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		[1] [2]	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2]	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

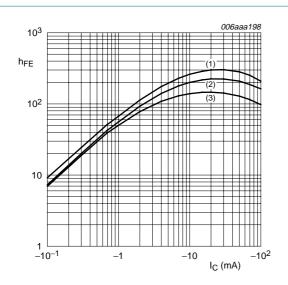
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

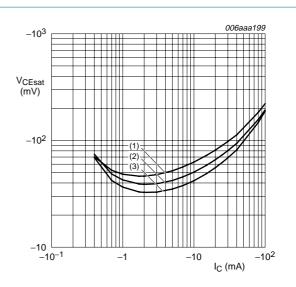
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-120	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
V _{I(off)}	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.8	-0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-2	-1.1	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω



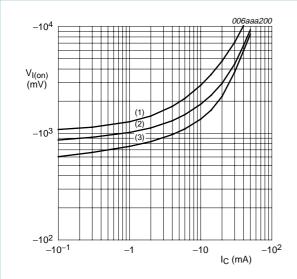
- $V_{CE} = -5 \text{ V}$
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

DC current gain as a function of collector Fig 1. current; typical values



- $I_{\rm C}/I_{\rm B} = 20$
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

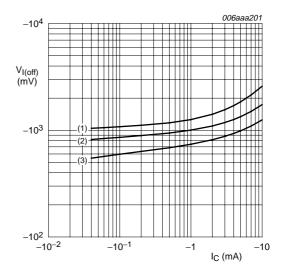
Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



- $V_{CE} = -0.3 \text{ V}$
- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Product data sheet

Fig 3. On-state input voltage as a function of collector current; typical values



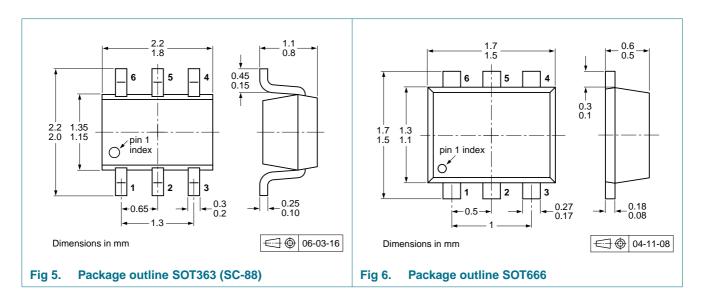
- $V_{CE} = -5 \text{ V}$
- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Off-state input voltage as a function of Fig 4. collector current; typical values

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PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description		Packing qua	ntity	
				3000	4000	10000
PEMB16	SOT666	4 mm pitch, 8 mm tape and reel;		-	-115	-
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

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PEMB16; PUMB16

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB16_PUMB16_3	20090831	Product data sheet	-	PEMB16_PUMB16_2		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 5 "Package outline SOT363 (SC-88)": updated 					
PEMB16_PUMB16_2	20050610	Product data sheet	-	PUMB16_1		
PUMB16_1	20031103	Product specification	-	-		

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB16; PUMB16

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